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QUANTUM FLUCTUATIONS IN THE TRANSMISSION OF A BALLISTIC METALLIC CONSTRICTION

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Abstract. We have studied fluctuations in the magnetoresistance of a small ballistic constriction as a function of the well defined excess energy of the electrons. A model based on quantum interference on a length scale given by the elastic mean free path is presented to explain the data.

The magnetoresistance of various mesoscopic systems with diffusive electronic transport exhibits reproducible fluctuations¹. These universal conductance fluctuations (UCF) result from quantum interference between elastically scattered electrons and have the property that their rms amplitude (of order e^2/h) is independent of sample size or degree of disorder. The phases of the electronic waves are shifted by an applied magnetic field resulting in a typical field scale $B_c \simeq \Phi_0/A$, a flux quantum $\Phi_0 = h/e$ through a phase coherent area A.

Here we report on reproducible fluctuations, similar in appearance as UCF, but observed in a ballistic point contact, a system with an elastic mean free path ℓ_e larger than the constriction radius a. The effective sample size of a point contact is about 2a, since an applied voltage V drops almost

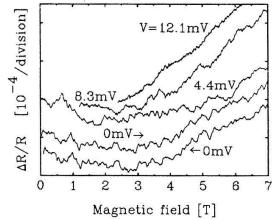


Fig.1 Magnetoresistance traces of an 11Ω Ag point contact for different applied voltages.

completely across the contact region². The transmission of such a point contact depends on the probability for an injected electron (energy eV) to return through the contact. Elastic (impurity, defects) or inelastic (electron-phonon) scattering events are responsible for this backscattering. The latter gives the possibility to study the energy dependence of the transmission what is known as point-contact spectroscopy². At low bias the scattering is completely elastic (phase coherent) allowing quantum-interference effects to be observable. The point contacts were fabricated using nanofabrication techniques and consist of two evaporated 200nm Ag layers seperated by a 20nm silicon nitride membrane in which a single hole (radius a~5nm) was patterned. In Fig. 1 we plotted magnetoresistance traces of an 11Ω Ag point contact for different voltages, measured at T=400mK. A reproducible fluctuation pattern (magnetofingerprint)

superimposed on a slowly varying background is observed. A change in bias changes the fingerprint completely (after $\Delta V \simeq 2mV$), the typical field scale B_c increases whereas the amplitude δG of the fluctuations decreases. At zero bias we find an amplitude $\delta G = 1.8 \times 10^{-2}e^2/h$, decreasing for temperatures above T=5K. In Fig. 2 we plotted the rms amplitude of the fluctuations as a function of the applied voltage together with the point-contact spectrum $d^2I/dV^2(V)$ of the same device. This spectrum is proportional to the point contact variant of the electron-phonon Eliashberg function $\alpha^2 F_p$. The clear resolved transverse (TA) and longitudinal (LA) acoustic phonon peaks together with the low background in the spectrum are a good indication that the transport through the contact is ballistic. A clear decrease in fluctuation amplitude δG at V=10mV coincides with the first phonon peak in the spectrum. From B_c , obtained from the halfwidth of the auto correlation function, we can calculate a characteristic size $L=(\Phi_0/B_c)^{1/2}$ of flux enclosing paths and find $L\simeq 245nm$ at zero bias and $L\simeq 65nm$ at V=12mV and higher. A comparison of L with radius $a\simeq 5nm$ (calculated from

the contact resistance $R_p = (4p_\ell/3\pi a^2)(1+0.82a/\ell_e)$) and elastic mean free path $\ell_e \approx 240nm$ (determined from the resistance ratio of an Ag layer and of the point contact itself) indicates that impur-

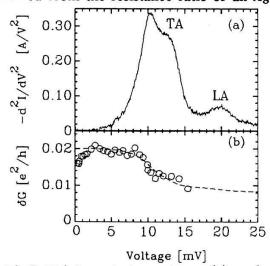


Fig.2 Point-contact spectrum (a) and rms amplitude δG as a function of bias (b). The dashed curve is calculated from the spectrum (see text).

ity scattering far away from the constriction area plays a minor role in the fluctuation phenomena. Following arguments of Lee³ we can estimate the rms amplitude of the fluctuations δG using the generalized Landauer equation for the conductance $G=(2e^2/h)\Sigma|t_{\alpha\beta}|^2$, where $|t_{\alpha\beta}|^2$ is the transmission probability from incoming channel a to outgoing channel β and the summation takes place over the number of channels $N=a^2k_F^2/4$. For a purely ballistic contact the transmission probability is $|t_{\alpha\beta}|^2 = \delta_{\alpha\beta}$. In the presence of elastic impurity scattering around the constriction the ensemble averaged transmission probability $|t_{\alpha\beta}|^2 = [1 - 0.82a/\ell_{\rm p}]/N$. By calculating the variance of the conductance transforming these transmission probabilities to reflection probabilities we find the T=0 rms amplitude of the fluctuations $\delta G \simeq 1.6(e^2/h)(a/\ell_{\rho})$, which depends on effective sample size and degree of disorder. With a=5nm and $\ell_{\rho}=240nm$ we find $\delta G=3.3 \ 10^{-2}e^2/h$ in fair agreement with the experimental zero bias result $\delta G = 1.8 \ 10^{-2} e^2/h$. The decrease of δG is explained by the enhanced electron-phonon interaction at 10mV and higher, leading to a

reduced inelastic mean free path L_{in} , which results in destruction of the phase coherence of the larger interference loops. To include inelastic processes in our above derived expression for δG we multiplied by $exp[-\ell_e/L_{in}]$, the probability that an electron is inelastically scattered on a length scale ℓ_e , and we plotted the result as a dashed line in Fig.2 (L_{in} can simply be calculated from the

spectrum). Because of the random distribution of impurities around the constriction the system lacks inversion symmetry, resulting in an asymmetric resistance with respect to a reversed bias1. This is clearly visible in Fig. 3 where the magnetofingerprint for V=0 evolutes to two different fingerprints for small positive and negative voltages. From the cross correlation of these curves we find a correlation voltage $V_c \simeq lmV$. Remarkably, δG is roughly constant up to l0mV, in contrast with diffusive mesoscopic systems, where for voltages exceeding V_c averaging over V/V_c coherent subsystems causes the amplitude δG to decrease. However, in a point contact the voltage drops off in the contact region and hence the impurity potential is not affected by the applied voltage. Therefor there is no averaging for $V>>V_C$, and δG remains constant. A comparison of the correlation energy $E_c \simeq \hbar/\tau$ (with τ the time to traverse a coherent electron trajectory, in our case $\tau \simeq \pi \ell_e / v_F$) with the observed correlation voltage V_c supp-

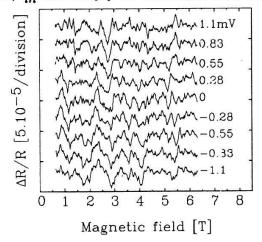


Fig.3 Magnetoresistance traces measured around V=0. The background has been substracted.

orts the idea of quantum interference on a length scale given by the elastic mean free path.

references.

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